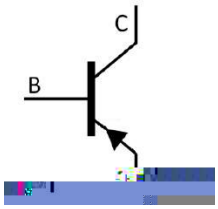
/ Descriptions

TO-92 PNP Silicon PNP transistor in a TO-92 Plastic Package.

h_{FE}

High h_{FE}.

General amplifier application.





PIN1 Base PIN 2 Collector PIN 3 Emitter

/ hFE Classifications & Marking

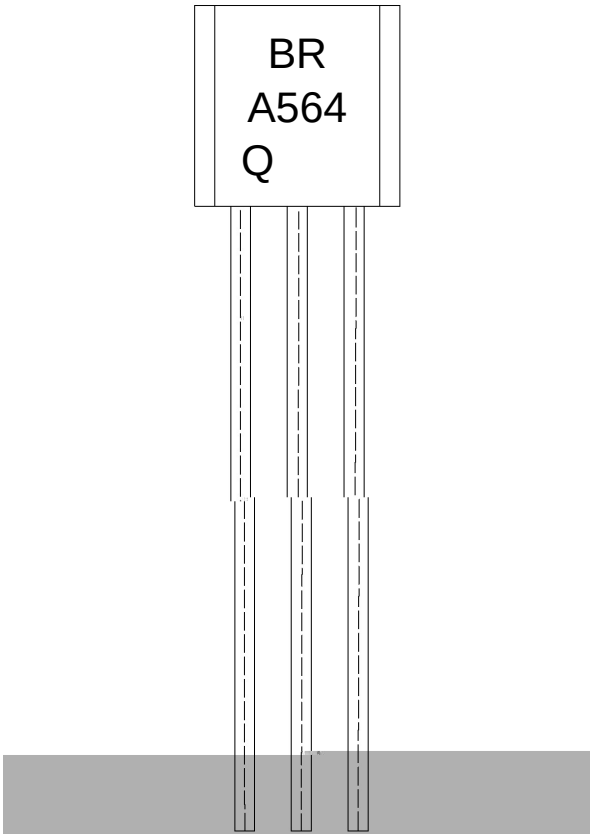
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol		Rating	Unit
Collector to Base Voltage	V_{CBO}	2SA564	-25	V
		2SA564A	-45	
Collector to Emitter Voltage	V_{CEO}	2SA564	-25	V
		2SA564A	-45	
Emitter to Base Voltage	V_{EBO}		-7.0	V
Collector Current - Continuous	I_C		-100	mA
Collector Current – Continuous(Pulse)	I_{CP}		-200	mA
Collector Power Dissipation	P_C		400	mW
Junction Temperature	T_j		150	
Storage Temperature Range	T_{stg}		-55 150	

/ Electrical Characteristics(Ta=25)

Parameter	Symbol		Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}		V_{CB}=-10V I_E=0		-0.001	-1.0	A
Collector Cut-Off Current	I_{CEO}		V_{CE}=-10V I_B=0			-10	A
Collector to Base Breakdown Voltage	V_{CBO}	2SA564	I_C=-10uA I_E=0	-25			V
		2SA564A		-45			
Collector to Emitter Breakdown Voltage	V_{CEO}	2SA564	I_C=-10uA I_E=0	-25			V
		2SA564A		-45			
Emitter to Base Breakdown Voltage	V_{EBO}		I_E=-10 A I_C=0	-5.0			V
DC Current Gain	h_{FE}		V_{CE}=-10V I_C=-2.0mA	130	250	520	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$		I_C=-100mA I_B=-10mA		-0.3		V
Output capacitance	C_{ob}		V_{CB}=-10V I_E=0 f=1.0MHz		3.5		pF

/ Marking Instructions



BR:

A564

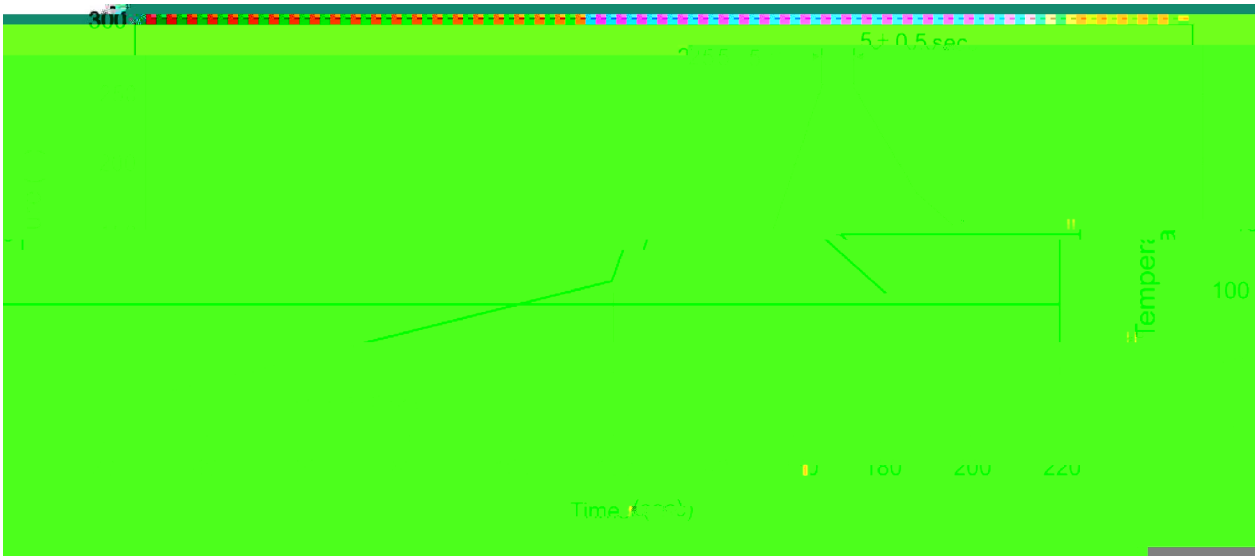
Q: h_{FE}

****

Note:

BR:	Company Code.
A564:	Product Type.
Q:	h_{FE} Classifications Symbol
****:	Lot No. Code,code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



				Note:	
1	25	150	60	90sec;	1.Preheating:25~150 , Time:60~90sec.
2	255±5			5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3		2	10	/sec.	3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270±5	10±1 sec.	Temp:270±5	Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units					Dimension		(unit mm3)

/ AMMO

Package Type	Units					Dimension	(unit mm3)

/ Notices